

Supporting Information

Efficient red perovskite quantum dots light emitting diode fabricated by inkjet printing

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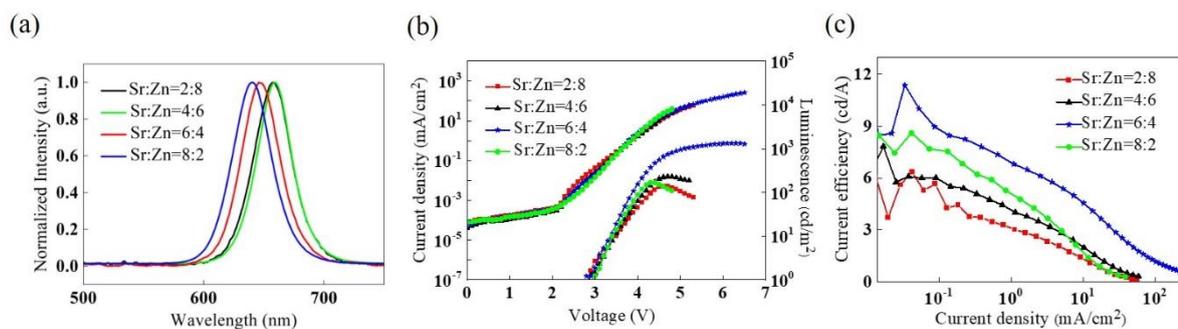


Figure S1. a) PL spectra of PeQDs solution with different ratio of Sr and Zn. b) J-V-L characteristics and c) LE-J characteristics of PeQD-LED with different ratio of Sr and Zn.

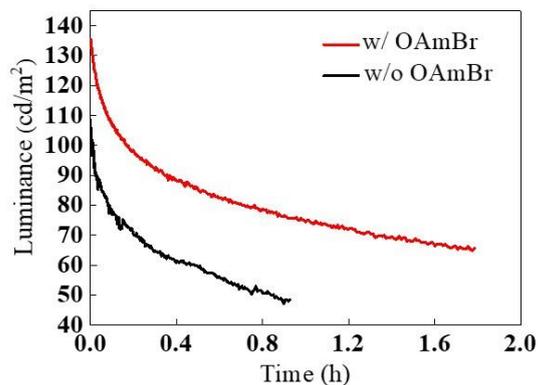


Figure S2. Lifetimes of the PeQD-LEDs with and without OAmBr.

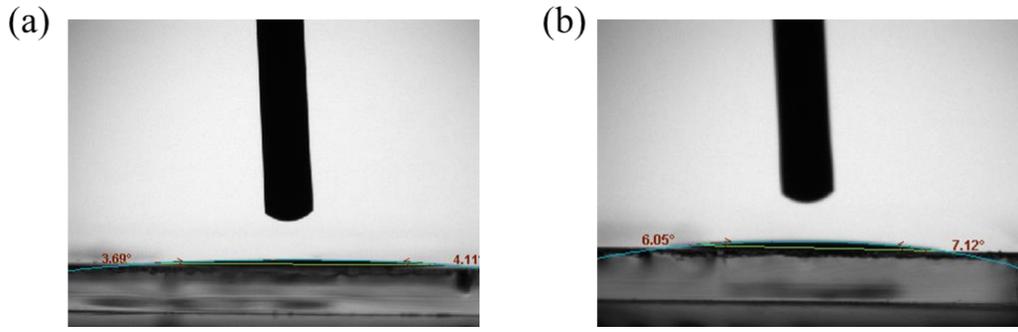


Figure S3. (a) contact angle of PeQD ink on PTAA substrate. (b) contact angle of PeQD ink with PB on PTAA substrate.

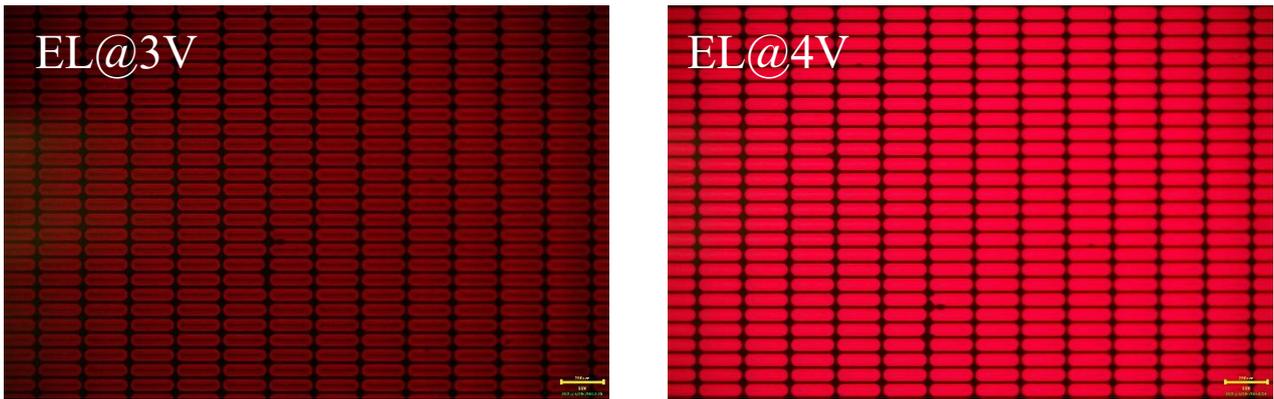


Figure S4. Light-on images of inkjet-printed matrix PeQD-LED with PB with a bias of 3V (left) and 4V (right) (scale bar: 200 μm).

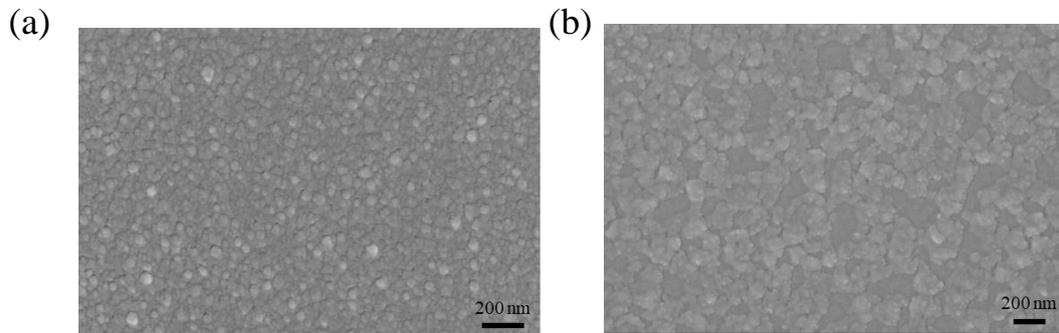


Figure S5. (a) SEM image of spin coated PeQD film on PTAA. (b) SEM image of inkjet-printed PeQD film on PTAA.

Table S1. The XPS elemental ratio of PeQD films with and without OAmBr

XPS results	Cs	Pb	I	Br	N
w/o OAmBr	15.30%	12.52%	35.77%	29.68%	6.73%
w/ OAmBr	14.74%	12.55%	32.22%	32.41%	8.08%